

## ABSTRACT OF THE DISCLOSURE

The invention comprises a chemical vapor deposition method of forming a barium strontium titanate comprising dielectric layer. A substrate is positioned within a reactor. Barium and strontium are provided within the reactor by flowing at least one metal organic precursor to the reactor. Titanium is provided within the reactor. At least one oxidizer is flowed to the reactor under conditions effective to deposit a barium strontium titanate comprising dielectric layer on the substrate. In one implementation, the oxidizer comprises  $H_2O$ . In one implementation, the oxidizer comprises  $H_2O_2$ . In one implementation, the oxidizer comprises at least  $H_2O$  and at least another oxidizer selected from the group consisting of  $O_2$ ,  $O_3$ ,  $NO_x$ ,  $N_2O$ , and  $H_2O_2$ , where "x" is at least 1. In one implementation, the oxidizer comprises at least  $H_2O_2$  and at least another oxidizer selected from the group consisting of  $O_2$ ,  $O_3$ ,  $NO_x$ , and  $N_2O$ , where "x" is at least 1.